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Magnetic properties and magnetocaloric effects of RNiSi₂ (R= Gd, Dy, Ho, Er, Tm) compounds

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Orthorhombic CeNiSi₂-type polycrystalline RNiSi₂ (R=Gd, Dy, Ho, Er, Tm) compounds were synthesized and the magnetic and magnetocaloric properties were investigated in detail. The transition temperatures of RNiSi₂ compounds are all in a very low temperature range (<30 K). As temperature increases, all of the compounds undergo an AFM to PM transition (GdNiSi2 at 18 K, DyNiSi2 at 25 K, HoNiSi₂ at 10.5 K, ErNiSi₂ at 3 K and TmNiSi₂ at 3.5 K, respectively). ErNiSi₂ compound shows the largest $(\Delta S_M)_{max}$ (maximal magnetic entropy change) among these compounds. The value of $(\Delta S_M)_{max}$ is 27.9 J/kgK under a field change of 0-5 T, which indicates that ErNiSi₂ compound is very competitive for practical applications in low-temperature magnetic refrigeration in the future. DyNiSi₂ compound shows large inverse MCE (almost equals to the normal MCE) below the T_N which results from metamagenitic transition under magnetic field. Considering of the normal and inverse MCE, DyNiSi₂ compound also has potential applications in low-temperature multistage refrigeration. © 2018 Author(s). All article content, except where otherwise noted, is licensed under a Creative Commons Attribution (CC BY) license (http://creativecommons.org/licenses/by/4.0/). https://doi.org/10.1063/1.5007018

I. INTRODUCTION

The magnetocaloric effect (MCE), a kind of physical phenomenon found more than 130 years ago, is one of the intrinsic properties of magnetic materials. Commercial and residential refrigeration, based on conventional gas compression/expansion technology, is a mature industry. However, the magnetic refrigeration (MR) based on MCE is becoming competitive with conventional gas compression/expansion technology because its environmental friendliness and high efficiency.^{1–5} In the last twenty years great progress has been made on exploring large MCE materials for applications at room temperature such as refrigerators and air conditioners.^{6,7} The typical room temperature MCE materials mainly include Gd₅Si₂Ge₂,^{8,9} La(Fe, Si)₁₃,¹⁰⁻¹⁴ MnAs_{1-x}Sb_x,¹⁵ MnFeP_{1-x}As_x,¹⁶ Heusler alloys,^{17,18} etc. MCE materials are generally evaluated by the following parameters: the maximum value of magnetic entropy change ($(\Delta S_M)_{max}$), the full width at half maximum of $\Delta S_M - T$ curve (δT_{FWHM}) , refrigerant capacity (RC) and adiabatic temperature change (ΔT_{ad}). For most MCE materials, the value of the ΔS_M is negative (normal MCE). But the positive ΔS_M which called inverse MCE also can be found in some materials such as TbNiGe2,¹⁹ TbMn0.33Ge2,²⁰ etc. Recently, much attention has also been paid on the MCE materials with low transition temperature because these materials are promising to be used for gas liquefaction in magnetic cooling cycle or combined magnetic-gas cooling cycle.^{6,21} These low temperature MCE materials mainly include the rare earth based intermetallic compounds such as RCo₂,^{22,23} RNi,²⁴ etc.



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Rare earth based intermetallic compounds have shown interesting magnetic properties and excellent performance on MCE. The ternary $RTSi_2$ series (R is rare earth, T is transition metal) is one category of rare earth based intermetallic compounds which has been intensively studied during the last decades.^{25–27} The results show that the compounds with R= Pr and Nd are ferromagnets and those with R= Gd, Tb, Dy, Ho, Er are antiferromagnets. Experimental results of electrical resistivity, Hall coefficient, magnetic susceptibility and specific heat for CeNiSi₂ support a theory of the Anderson lattice.²⁸ Neutron diffraction and magnetic measurements on RNiSi₂ compounds where R= Pr and Nd give refined atomic position parameters and it is found that the preferred moment direction is along the c axis.²⁹ The same measurements on RNiSi₂ compounds where R= Tb, Dy, Ho, Er show that the compounds all have uniaxial moment arrangements and have almost the same easy axis, the shortest axis c, except for ErNiSi₂ with an easy axis of a axis.^{30–33}

Considering the lack of research work on MCE of RNiSi₂ compounds, further study on magnetic properties and MCE will be performed. In this paper, the polycrystalline RNiSi₂ (R=Gd, Dy, Ho, Er, Tm) compounds were synthesized. The magnetic properties and MCE which both contains normal and inverse effects were investigated in detail.

II. EXPERIMENTAL PROCEDURE

The polycrystalline RNiSi₂ (R=Gd, Dy, Ho, Er, Tm) compounds were prepared by arc-melting appropriate proportion of constituent components with the purity better than 99.9% in a water-cooled copper hearth in a high-purity argon atmosphere. The ingots were turned over after each melting and re-melted several times to ensure the compositional homogeneity. After arc-melting, the ingots were wrapped by molybdenum foil respectively and sealed in a high-vacuum quartz tube, annealed at 1273K for 25 days, finally quenched into liquid nitrogen. The crystal structure was characterized by powder X-ray diffraction (XRD) method with Cu K α radiation. Magnetic measurements including the temperature dependence of magnetization (M-T) and the field dependence of magnetization (M-H) curves were performed by employing Vibrating Sample Magnetometer with Quantum Design (SQUID-VSM). Heat capacity measurements were carried out by employing Physical Properties Measurement System (PPMS).

III. RESULTS AND DISCUSSION

The XRD pattern of RNiSi₂ (R=Gd, Dy, Ho, Er, Tm) compounds at room temperature and its crystal structure are shown in Fig. 1. Almost all of the diffraction peaks can be indexed to an



FIG. 1. The XRD patterns of RNiSi₂ (R= Gd, Dy, Ho, Er, Tm) compounds measured at room temperature. The inset is the crystal structure of RNiSi₂.

orthorhombic CeNiSi₂-type structure (space group Cmcm #63). The result is in accord with previous work.²⁶ The Bragg positions are marked at the bottom of the picture. It can also be seen that there is a small peak around 37.5° for all compounds and a peak around 34.5° for GdNiSi₂ and DyNiSi₂ compound, which indicates that small amount of impurity may exist. The impurity is indexed as RNiSi₃. However, it does not affect our discussions and conclusions because the amount of impurity is not large. As the atom number of R increases, the position of diffraction peaks moves towards higher angle range, which indicates that the lattice constant becomes smaller from GdNiSi₂ to TmNiSi₂ compound.

The Zero-Field-Cooled (ZFC) and Field-Cooled (FC) magnetization curves for RNiSi₂ compounds were measured under a field of 0.01 T. They are shown in Fig. 2(a)–(d). The MH curves for RNiSi₂ compounds are also shown in Fig. 2(e)–(h). The MT for DyNiSi₂ shows a rapid increase and then a decrease with the increasing temperature, which indicates that this compound undergoes a simple transition from antiferromagnetic (AFM) to paramagnetic (PM) phase. The same conclusion can also be found in MH curves. The transition temperature is determined to be $T_N=25$ K. The overlap of ZFC and FC curves around T_N shows a good thermal reversibility in this compound. From MH curve we can see the compound occurs metamagenetic transition with the field increasing. All of the features mentioned above can also be found in other compounds. The transition temperatures along with the effective magnetic moments, which have been calculated according to the Curie-Weiss Law, are shown in Table I. The effective moment and ion moment is almost the same for each compound, indicating only rare earth atoms contribute to the magnetic moments in this series of compounds. It reveals from Fig. 2 that the value of the transition temperature (T_N) shows a decreasing trend when the atomic number of rare earth atom increases. However, there is an exception for TmNiSi₂, which may result from the complex magnetic coupling in TmNiSi₂ compound.

The MCE materials are generally evaluated by isothermal magnetic entropy change (ΔS_M) , which is calculated from isothermal magnetization data (M-H curves) by using Maxwell relation: $\Delta S_M = \int_0^H (\partial M / \partial T)_H dH$. The temperature dependences of ΔS_M under a field change of 0-2 T and 0-5 T for RNiSi₂ compounds are shown in Fig. 3(a)–(d), respectively. The results shows that all compounds show normal MCE because the value of ΔS_M is negative around transition temperatures



FIG. 2. The MT and MH curves of RNiSi₂ (R= Dy, Ho, Er, Tm) compounds, respectively. (a) MT for DyNiSi₂. (b) MT for HoNiSi₂. (c) MT for ErNiSi₂. (d) MT for TmNiSi₂. (e) MH for DyNiSi₂. (f) MH for HoNiSi₂. (g) MH for ErNiSi₂. (h) MH for TmNiSi₂.

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				0-2T			0-5T		
Materials	$T_N(K)$	$M_{eff}(\mu_B)$	$M_{ion}(\mu_B)$	$\frac{-(\Delta S_M)_{max}}{(J/kg \ K)}$	$\delta T_{FWHM}(K)$	RC(J/kg)	$\frac{-(\Delta S_M)_{max}}{(J/kg \ K)}$	$\delta T_{FWHM}(K)$	RC(J/kg)
GdNiSi ₂	18.0	8.2	7.8	0.7	20.2	9.9	3.5	21.2	58.0
DyNiSi ₂	25.0	10.7	10.5	0.7	15.3	8.6	4.4	15.8	59.0
DyNiSi ₂	-	-	-	(-2.5)	-	31.6	(-3.6)	-	90.5
HoNiSi ₂	10.5	11	10.6	5.3	8.9	35.4	16.8	15.6	198.8
ErNiSi2	3.0	9.1	9.6	17.0	-	75.8	27.9	-	225.3
TmNiSi ₂	3.5	7.0	7.1	12.3	7.5	71.2	16.4	17.2	222.6
ErMn ₂ Si ₂ ³⁴	4.5	-	-	20.0	-	130	25.2	-	365
TmCuAl ³⁵	2.8	-	-	17.2	-	129	24.3	-	372
ErNi2Si236	3.5	-	-	15.1	-	-	22.9	-	-
ErNiSi ³⁷	3.2			8.8			19.1		309

TABLE I. The transition temperatures, effective magnetic moments, ion magnetic moments and magnetocaloric parameters of RNiSi₂ (R= Gd, Dy, Ho, Er, Tm) compounds and other compounds.

for each of them. However, HoNiSi₂ shows small inverse MCE below the transition temperature and DyNiSi₂ shows large inverse MCE (almost equals to the normal MCE) below the transition temperature which will be discussed in detail in the following section. It can be observed from Fig. 3 that all of the curves have a large peak and the maximal magnetic entropy change ($(\Delta S_M)_{max}$) occurs around T_N. The refrigerant capacity (RC) is another important parameter to evaluate MCE materials. The value of RC can be calculated by using the approach $RC = \int_{T_1}^{T_2} |\Delta S_M| dT$, where T₁ and T₂ are the temperatures corresponding to the full width at the half value of (ΔS_M)_{max}, respectively. And we call $\delta T_{FWHM} = T_2 - T_1$ the refrigerant temperature width. The (ΔS_M)_{max}, RC and δT_{FWHM} of RNiSi₂ compounds under a field change of 0-2 T and 0-5 T are calculated and shown in Table I. The MCE parameters of some low temperature MCE materials are also shown in Table I for comparison.^{34–37} For ErNiSi₂ compound, the value of (ΔS_M)_{max} is 17.0 J/kgK for 0-2 T and 27.9 J/kgK for 0-5 T



FIG. 3. The temperature dependences of ΔS_M at a field change of 0-2 T and 0-5 T for RNiSi₂ (R= Dy, Ho, Er, Tm) compounds, respectively. (a) DyNiSi₂. (b) HoNiSi₂. (c) ErNiSi₂. (d) TmNiSi₂.

respectively, which are comparable or even larger than those of other listed materials. The RC of ErNiSi₂ compound is approximately calculated to be 75.8 J/kg for 0-2 T and 225.3 J/kg for 0-5 T, respectively, where the integration starts with the temperature of 2 K. These values are not accurate because the actual low temperature boundary of δT_{FWHM} is far lower than 2 K for ErNiSi2 compound. According to the model proposed by Oesterrreicher et al.³⁸ The $(\Delta S_M)_{max}$ is positively correlated with the total angular momentum quantum number (J) and negatively correlated with magnetic ordering temperature. In this series, HoNiSi₂ compound shows the largest J, but its Neel temperature is much larger than that of ErNiSi₂ compound. Considering that HoNiSi₂ and ErNiSi₂ have a similar J, the value of Neel temperature exerts a main effect on the value of $(\Delta S_M)_{max}$. As a result, ErNiSi₂ compound shows the largest ($\Delta S_M)_{max}$ among RNiSi₂ compounds. The excellent MCE performance of ErNiSi₂ compound indicates its potential applications in low temperature refrigeration.

The Fig. 3 also shows that DyNiSi₂ and HoNiSi₂ compounds both have positive ΔS_M below T_N , which called inverse MCE. This phenomenon results from the mixed exchange interaction and the applied magnetic field leads to a further spin-disordered state,³⁹ which occurs metamagenitic transition. This makes $\partial M/\partial T$ positive under T_N. For HoNiSi₂ compound, the positive ΔS_M can only be found under a low field change and the value of positive ΔS_M is far smaller than the absolute value of negative ΔS_M around T_N. When the field change is 5T, the positive ΔS_M has been disappeared, which indicates that the AFM ground state of HoNiSi2 compound below T_N is relatively weak. The same phenomenon can also be found in many Heusler alloys and AFM magnetocaloric effect materials.³⁹ However, for DyNiSi₂ compound, the inverse MCE can even be found in a high field change such as 5T and the maximal positive ΔS_M is almost equals to the maximal negative ΔS_M . For further study, heat capacity was measured and ΔS_M also calculated using heat capacity data through the expression $\Delta S_M = \int_0^H \{ [C(T, H) - C(T, 0)]/T \} dT$. The results all shown in Fig. 4. The Fig. 4 shows that the curves obtained using magnetization data are in good agreement with the corresponding curves obtained using heat capacity. And the field change of the maximal positive ΔS_M occurs is about 3.6T. The large inverse MCE results from the strong AFM coupling in DyNiSi₂ compounds which may be related to the large magnetocrystalline anisotropy of Dy atoms. The inverse MCE can also be used for magnetic refrigeration if only the refrigerator works in a reverse process. For example, for DyNiSi₂ compound, magnetic refrigeration can be realized in a usual working recycle around 25K and it can be used in a reverse working recycle around 15K, which seems useful in multistage refrigeration. And the RC of DyNiSi2 compound is re-calculated by considering of the contribution of inverse MCE at lower temperatures which also shown in Table I. The value of RC for a field change of 0-5 T is modified from 59 J/kg and 90.5 J/kg.



FIG. 4. The temperature dependences of ΔS_M for DyNiSi₂ compound calculated from magnetization and heat capacity data for field changes of 0-1T, 0-2T, 0-3T, 0-4T, and 0-5T, respectively. The inset shows the field change dependences of $(\Delta S_M)_{max}$ for inverse MCE at 15.5K.

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The excellent performance of DyNiSi₂ compound indicates its potential applications in low temperature refrigeration.

IV. CONCLUSION

In summary, all orthorhombic CeNiSi₂-type polycrystalline RNiSi₂ (R=Gd, Dy, Ho, Er, Tm) compounds are AFM ordered and T_N in a very low temperature. Among these compounds, ErNiSi₂ compound shows the largest $(\Delta S_M)_{max}$ and RC, which is larger than almost all of the materials in this low temperature range, indicating its potential practical applications in low-temperature magnetic refrigeration in the future. DyNiSi₂ compound shows large inverse MCE (almost equals to the normal MCE) below the T_N which results from metamagenitic transition under magnetic field. Considering of the normal and inverse MCE, DyNiSi₂ compound also has potential applications in low-temperature multistage refrigeration.

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